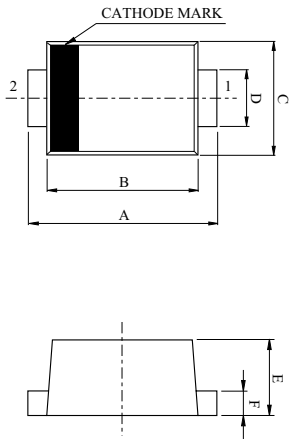
KDV214VA

VARIABLE CAPACITANCE DIODE
SILICON EPITAXIAL PLANAR DIODE

TV TUNING.

FEATURES

- High Capacitance Ratio : C2V/C25V=6.3(Min.)
- Low Series Resistance : r_S=0.57 Ω(Max.)
- Excellent C-V Characteristics, and Small Tracking Error.
- Useful for Small Size Tuner.



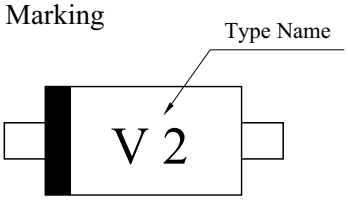
DIM	MILLIMETERS
A	1.4±0.05
B	1.0±0.05
C	0.6±0.05
D	0.28±0.03
E	0.5±0.05
F	0.12±0.03

VSC

MAXIMUM RATING (Ta=25℃)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Reverse Voltage	V_R	32	V
Junction Temperature	T_j	125	℃
Storage Temperature Range	T_{stg}	-55～125	℃

Marking



ELECTRICAL CHARACTERISTICS (Ta=25℃)

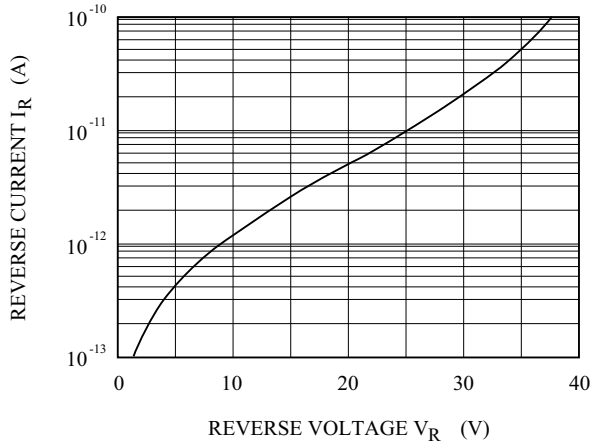
CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Reverse Current	I_R	V_R=28V	-	-	10	nA
Capacitance	C_{2V}	V_R=2V, f=1MHz	14.15	-	15.75	pF
Capacitance	C_{25V}	V_R=25V, f=1MHz	2.06	-	2.35	pF
Capacitance Ratio	C_{2V}/C_{25V}		6.3	-	-	-
Series Resistance	r_S	V_R=5V, f=470MHz	-	-	0.57	Ω

Note : Available in matched group for capacitance to 2.0%.

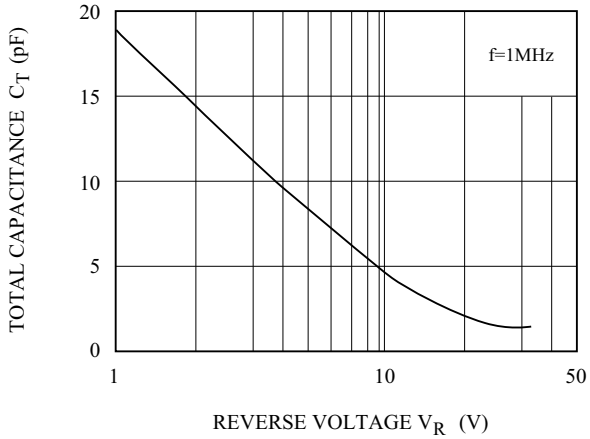
$$\frac{C(Max.)-C(Min.)}{C(Min.)} \leqq 0.02$$

(V_R=2~25V)

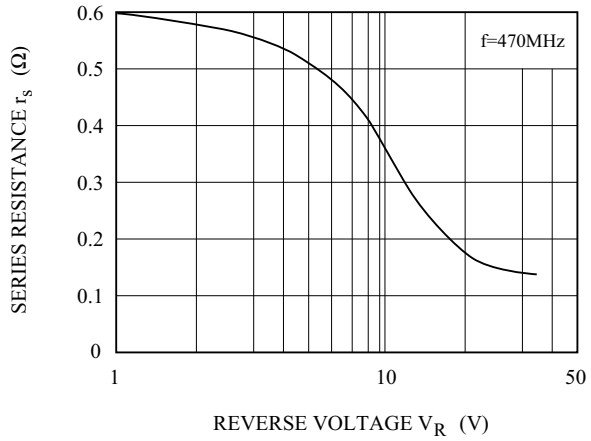
I_R - V_R



C_T - V_R



r_s - V_R



$\Delta(LOG\ C_T) / \Delta(LOG\ V_R)$ - V_R